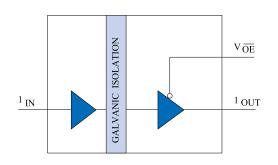


High Speed Digital Isolator

Functional Diagram



Truth Table

V _I	$V_{\overline{OE}}$	Vo
L	L	L
Н	L	Н
L	Н	Z
Н	Н	Z

Ordering Information

Model	Package Type						
	8–PDIP	8–SOIC					
IL710	-2	-3					

IL710-2 is an 8–PDIP package **IL710-3** is an 8–SOIC package

If requesting tape and reel, please specify as TR.

Example: IL710-3TR

Features



- · +5V and +3.3V CMOS/TTL Compatible
- * 2 ns Typical Pulse Width Distortion
- 4 ns Typical Propagation Delay Skew
- 10 ns Typical Propagation Delay
- ' High Speed: 110 MBd Typical
- · 30 kV/µs Typical Common Mode Rejection
- · Tri State Output
- 2500V_{RMS} Isolation (1 min.)
- * UL1577 Approved (File # E207481)
- IEC 61010-1 Approved (Report # 607057)

Applications

- · Digital Fieldbus Isolation
- Multiplexed Data Transmission
- · Computer Peripheral Interface
- · Noise Reduction in High Speed Digital Systems
- · Isolated Data Interfaces
- · Logic Level Shifting

Description

The IL710 is a CMOS digital isolator integrated with NVE's patented* IsoLoop® technology, which gives the IL710 high speed performance and excellent transient immunity specifications. The symmetric magnetic coupling barrier gives this device a typical propagation delay of only 10 ns and a pulse width distortion of 2 ns, giving the IL710 the best specifications of any isolator device. The IL710 also has a 100 Mbaud data rate, making it the world's fastest digital isolator. The IL710 is ideally suited for isolating such applications as PROFIBUS, RS-485, RS422, etc. It is available in 8-pin PDIP and 8-pin SOIC packages, and is specified over the temperature range of -40°C to +100°C without any performance derating.

Isoloop® is a registered trademark of NVE Corporation * US Patent number 5,831,426; 6,300,617 and others

IL710 IsoLoor®

Absolute Maximum Ratings

Parameters	Symbol	Min.	Max.	Units
Storage Temperature	T_S	-55	175	°C
Ambient Operating Temperature ⁽¹⁾	T _A	-55	125	°C
Supply Voltage	V_{DD1}, V_{DD2}	-0.5	7	Volts
Input Voltage	V _I	-0.5	V _{DD1} +0.5	Volts
Input Voltage	V _{OE}	-0.5	V _{DD2} +0.5	Volts
Output Voltage	V _O	-0.5	V _{DD2} +0.5	Volts
Output Current Drive	I _O		10	mA
Lead Solder Temperature (10s)			260	°C
ESD	2kV Human Body Model			

Recommended Operating Conditions

commended operating contains				
Parameters	Symbol	Min.	Max.	Units
Ambient Operating Temperature	T _A	-40	100	°C
Supply Voltage	$V_{\mathrm{DD1}}, V_{\mathrm{DD2}}$	3.0	5.5	Volts
Logic High Input Voltage	V _{IH}	2.4	V_{DD1}	Volts
Logic Low Input Voltage	V _{IL}	0	0.8	Volts
Minimum Signal Rise and Fall Times	t _{IR} ,t _{IF}		1	μsec

Insulation Specifications

Parameter	Condition	Min.	Тур.	Max.	Units
Barrier Impedance			>1014 3		$\Omega \parallel pF$
Constant Distant (Festivanal)		7.036 (PDIP)			mm
Creepage Distance (External)		4.026 (SOIC)			
Leakage Current	$240 V_{RMS}$		0.2		μΑ
Leakage Current	60Hz				

Package Characteristics

ackage characteristics						
Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Capacitance (Input-Output)(5)	C _{I-O}		1.1		pF	f= 1MHz
Thermal Resistance (PDIP)	$\theta_{ m JCT}$		150		°C/W	Thermocouple located at
(SOIC)	θ_{JCT}		240		°C/W	center underside of package
Package Power Dissipation	P_{PD}			150	mW	

IEC61010-1

TUV Certificate Numbers: B 01 07 44230 001 (PDIP) B 01 07 44230 002 (SOIC)

Classification as Table 1.

Model	Pollution	Material	Max Working	Package Type	
	Degree	Group	Voltage	8–PDIP	8–SOIC
IL710-2	II	III	300 Vrms	✓	
IL710-3	II	III	150 Vrms		✓

<u>UL 1577</u>

Component Recognition program. File # E207481

Rated 2500Vrms for 1min.

Electrical Specifications

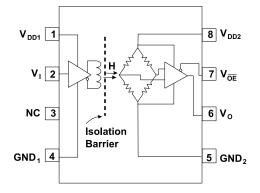
Electrical Specifications are $T_{\mbox{\footnotesize min}}$ to $T_{\mbox{\footnotesize max}}$ unless otherwise stated.

Parameter	Symbol	3.3 Volt	Specificat	ions	5Vol	t Specifica	tions	Units	Test Conditions
DC Specifications		Min.	Тур.	Max.	Min.	Тур.	Max.		
Input Quiescent Supply Current	I_{DD1}		8	10		10	15	μΑ	
Output Quiescent Supply Current	I_{DD2}		3.3	4		5	6	mA	
Logic Input Current	I _I	-10		10	-10		10	μΑ	
Logic High Output Voltage	V _{OH}	V _{DD2} -0.1 0.8*V _{DD2}			$V_{\rm DD2}$ -0.1 0.8* $V_{\rm DD2}$	$\begin{matrix}V_{DD2}\\V_{DD2}\text{-}0.5\end{matrix}$		V	$I_O = -20 \mu A, V_I = V_{IH}$ $I_O = -4 \text{ mA}, V_I = V_{IH}$
Logic Low Output Voltage	V _{OL}		0 0.5	0.1 0.8		0 0.5	0.1 0.8	V	$I_O = 20 \mu A, V_I = V_{IL}$ $I_O = 4 mA, V_I = V_{IL}$
Switching Specifications									
Maximum Data Rate		100	110		100	110		MBd	$C_L = 15 \text{ pF}$
Pulse Width	PW	10			10			ns	
Propagation Delay Input to Output (High to Low)	t _{PHL}		12	18		10	15	ns	$C_L = 15 \text{ pF}$
Propagation Delay Input to Output (Low to High)	t _{PLH}		12	18		10	15	ns	$C_L = 15 \text{ pF}$
Propagation Delay Enable to Output (High to High Impedance)	t _{PHZ}		3	5		3	5	ns	$C_L = 15 \text{ pF}$
Propagation Delay Enable to Output (Low to High Impedance)	t _{PLZ}		3	5		3	5	ns	$C_L = 15 \text{ pF}$
Propagation Delay Enable to Output (High Impedance to High)	t _{PZH}		3	5		3	5	ns	$C_L = 15 \text{ pF}$
Propagation Delay Enable to Output (High Impedance to Low)	t _{PZL}		3	5		3	5	ns	$C_{\rm L} = 15 \text{ pF}$
Pulse Width Distortion(2)			2	3		2	3		
Propagation Delay Skew ⁽³⁾	t _{PSK}		4	6		4	6	ns	$C_L = 15 \text{ pF}$
Output Rise Time (10-90%)	t _R		2	4		1	3	ns	$C_L = 15 \text{ pF}$
Output Fall Time (10-90%)	t _F		2	4		1	3	ns	$C_L = 15 \text{ pF}$
Common Mode Transient Immunity (Output Logic High or Logic Low) (4)	CMH	20	30		20	30		kV/μs	Vcm = 300V

Pin Connections

1	V_{DD1}	Input Power Supply
2	V _I	Logic Input Signal
3	NC	No Internal Connection
4	GND ₁	Input Power Supply Ground
5	GND ₂	Output Power Supply Ground
6	V_0	Output Logic Signal
7	$V_{\overline{OE}}$	Logic Output Enable*
8	V_{DD2}	Output Power Supply

^{*}Held Low Internally



IL710 IsoLoop®

Notes:

- Absolute Maximum ambient operating temperature means the device will not be damaged if operated under these conditions. It does not guarantee performance.
- 2. PWD is defined as $|t_{PHL} t_{PLH}|$. %PWD is equal to the PWD divided by the pulse width.
- 3. t_{PSK} is equal to the magnitude of the worst case difference in t_{PHL} and/or t_{PLH} that will be seen between units at 25°C.
- 4. ${\rm CM_H}$ is the maximum common mode voltage slew rate that can be sustained while maintaining Vo > 0.8 V_{DD2}. ${\rm CM_L}$ is the maximum common mode input voltage that can be sustained while maintaining Vo < 0.8 V. The common mode voltage slew rates apply to both rising and falling common mode voltage edges.
- 5. Device is considered a two terminal device: pins 1-4 shorted and pins 5-8 shorted.

Application Notes:

Power Consumption

Isoloop® devices achieve their low power consumption from the manner by which they transmit data across the isolation barrier. By detecting the edge transitions of the input logic signal and converting these to narrow current pulses a magnetic field is created around the GMR Wheatstone bridge. Depending on the direction of the magnetic field, the bridge causes the output comparator to switch following the input logic signal. Since the current pulses are narrow, about 2.5ns wide, the power consumption is independent of mark-to-space ratio and solely dependent on frequency. This has obvious advantages over optocouplers whose power consumption is heavily dependent on its on-state and frequency.

The approximate power supply current per channel for

Isoloop® is:
$$I(input) = 40 \left(\frac{f}{fmax}\right) \left(\frac{1}{4}\right) mA$$

where f = operating frequency fmax = 50 MHz

Power Supplies

It is recommended that low ESR ceramic capacitors be used to decouple the supplies. 10nF capacitors should be placed as close to the device as possible between $V_{\rm DD1}$ and GND_1 as well as between $V_{\rm DD2}$ and GND_2 .

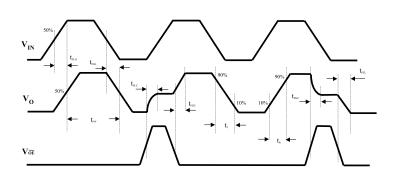
Signal Status on Start-up and Shut Down

To minimize power dissipation, the input signal to the IL710 is differentiated and then latched on the output side of the isolation barrier to reconstruct the signal. This could result in an ambiguous output state depending on power up, shutdown and power loss sequencing. Therefore, the designer should consider the inclusion of an initialization signal in his start-up circuit.

Electrostatic Discharge Sensitivity

This product has been tested for electrostatic sensitivity to the limits stated in the specifications. However, NVE recommends that all integrated circuits be handled with appropriate care to avoid damage. Damage caused by inappropriate handling or storage could range from performance degradation to complete failure.

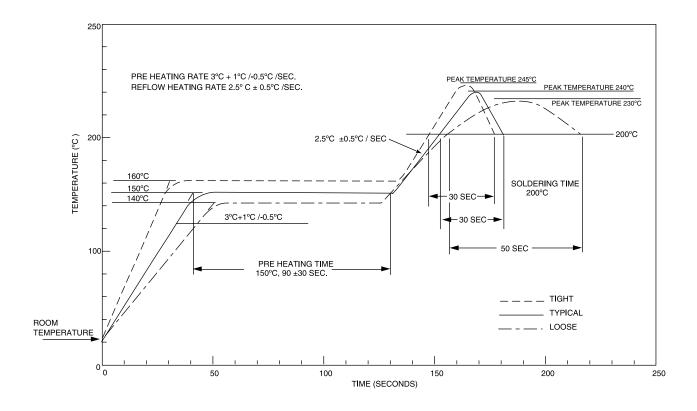
Timing Diagram



Legend

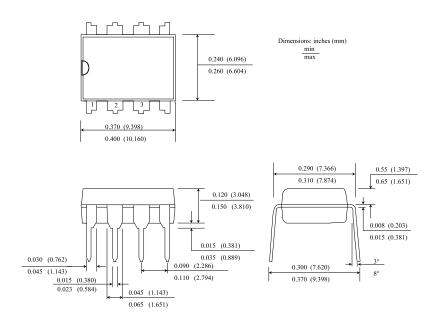
t _{PLH}	Propagation Delay, Low to High
$t_{ m PHL}$	Propagation Delay, High to Low
$t_{\rm PW}$	Minimum Pulse Width
t_{PLZ}	Propagation Delay, Low to High Impedance
t_{PZH}	Propagation Delay, High Impedance to High
t_{PHZ}	Propagation Delay, High to High Impedance
t_{PZL}	Propagation Delay, High Impedance to Low
t _R	Rise Time
t _E	Fall Time

IR Soldering Profile

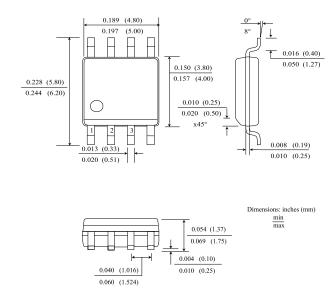


IL710

IL710-2 (8-Pin PDIP Package)

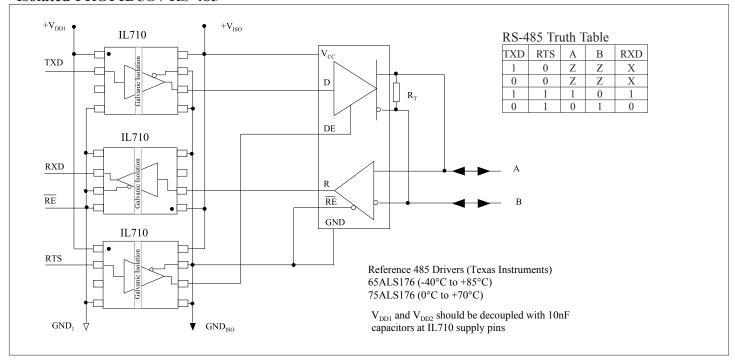


IL710-3 (Small Outline SOIC-8 package)

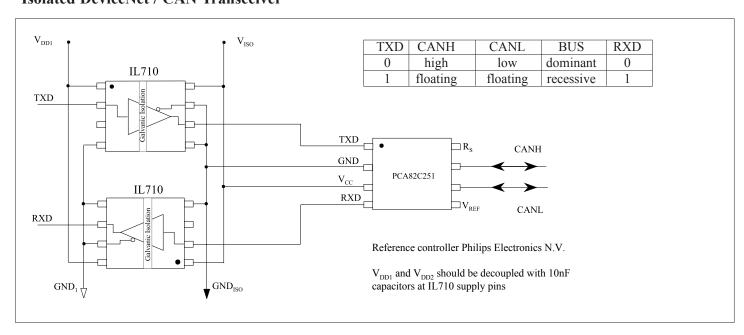


Applications

Isolated PROFIBUS / RS-485



Isolated DeviceNet / CAN Transceiver



About NVE

An ISO 9001 Certified Company

NVE Corporation is a high technology components manufacturer having the unique capability to combine leading edge Giant Magnetoresistive (GMR) materials with integrated circuits to make high performance electronic components. Products include Magnetic Field Sensors, Magnetic Field Gradient Sensors (Gradiometer), Digital Magnetic Field Sensors, Digital Signal Isolators and Isolated Bus Transceivers.

NVE is a leader in GMR research and in 1994 introduced the world's first products using GMR material, a line of GMR magnetic field sensors that can be used for position, magnetic media, wheel speed and current sensing.

NVE is located in Eden Prairie, Minnesota, a suburb of Minneapolis. Please visit our Web site at www.nve.com or call 952-829-9217 for information on products, sales or distribution.

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Specifications shown are subject to change without notice.

ISB-DS-001-IL710-E February 2002